

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

NISHIMOTO et al

Serial No.: 08/897,839

Filed: July 21, 1997

For: STRESS-ADJUSTED INSULATING
FILM FORMING METHOD,
SEMICONDUCTOR DEVICE AND
METHOD OF MANUFACTURING THE
SAME



Group Art Unit: 2814

Examiner: K. Eaton

ATTENTION AU 2814
EXPEDITED PROCESSING
RESPONSE TO FINAL ACTION

2018(2)
2-13-00
C. Eaton

A. Squell
1-12-01

RESPONSE TO FINAL ACTION OF JULY 5, 2000

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

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DEC 12 2000

TECHNOLOGY CENTER 2800

Responsive to the "final" rejection of July 5, 2000, please
amend the captioned application as follows:

IN THE CLAIMS:

Please cancel all pending claims and substitute therefor the
following new claims 43-52:

- 43. A stress-adjusted insulating film forming method for forming
a multilayered insulating film on a substrate, said method
comprising:

(a) forming a first insulating layer with a first type of
stress;

(b) forming a conductive interconnection layer on and in